SPN2304W
N-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPN2304W is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits, and low in-line power loss are needed in a very small outline surface mount package.

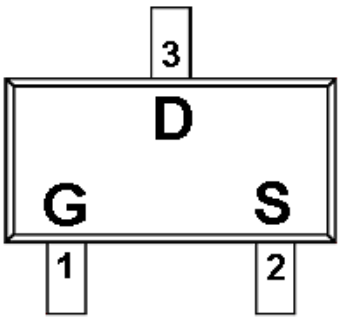
APPLICATIONS

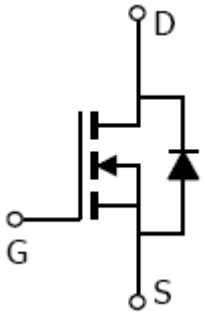
- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

FEATURES

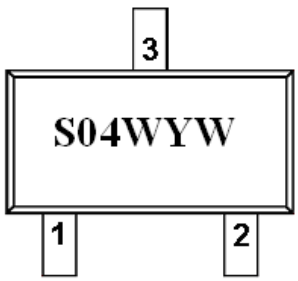
- 30V/3.2A,$R_{DS(ON)}$=65mΩ@V_{GS}=10V
- 30V/2.0A,$R_{DS(ON)}$=90mΩ@V_{GS}=4.5V
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23 package design

PIN CONFIGURATION(SOT-23)





PART MARKING



Y : Year Code
W : Week Code

SPN2304W
N-Channel Enhancement Mode MOSFET

PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN2304WS23RGB	SOT-23	S04W

※ Week Code : A ~ Z(1 ~ 26) ; a ~ z(27 ~ 52)
※ SPN2304WS23RGB : Tape Reel ; Pb – Free ; Halogen - Free

ABSOULTE MAXIMUM RATINGS

(T_A=25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	30	V
Gate –Source Voltage		V_{GSS}	±20	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	3.2	A
	T_A=70℃		2.6	
Pulsed Drain Current		I_{DM}	10	A
Continuous Source Current(Diode Conduction)		I_S	1.25	A
Power Dissipation	T_A=25℃	P_D	1.25	W
	T_A=70℃		0.8	
Operating Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	100	℃/W

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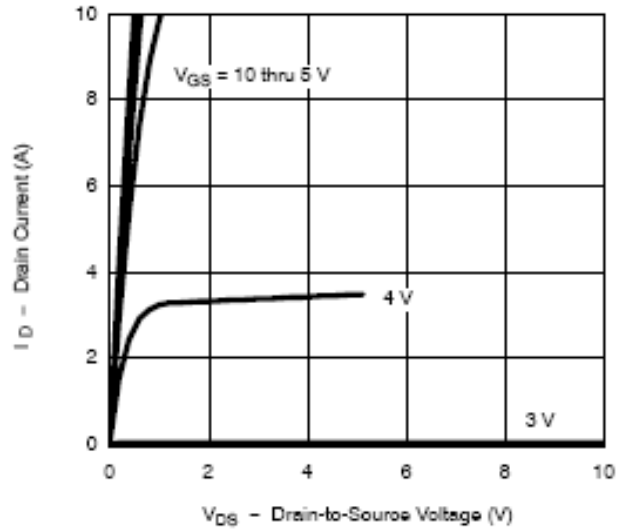
ELECTRICAL CHARACTERISTICS

(T_A=25℃ Unless otherwise noted)

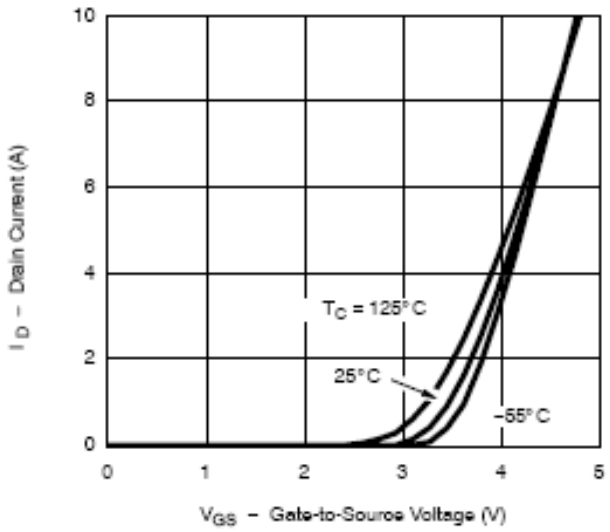
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	1.0		3.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=24V,V_{GS}=0.0V			1	uA
		V_{DS}=24V,V_{GS}=0.0V T_J=55℃			10	
On-State Drain Current	$I_{D(on)}$	V_{DS}≧4.5V,V_{GS}=10V	6			A
		V_{DS}≧4.5V,V_{GS}=4.5V	4			
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=3.2A		0.050	0.065	Ω
		V_{GS}=4.5V,I_D=2.0A		0.065	0.090	
Forward Transconductance	gfs	V_{DS}=4.5V,I_D=2.5A		4.6		S
Diode Forward Voltage	V_{SD}	I_S=1.25A,V_{GS}=0V		0.82	1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=15V_{GS}=10V I_D=2.5		4.5	10	nC
Gate-Source Charge	Q_{gs}			0.8		
Gate-Drain Charge	Q_{gd}			1.0		
Input Capacitance	C_{iss}	V_{DS}=15V_{GS}=0V f=1MHz		240		pF
Output Capacitance	C_{oss}			110		
Reverse Transfer Capacitance	C_{rss}			17		
Turn-On Time	$t_{d(on)}$	V_{DD}=15R_L=15 I_D=1.0A,V_{GEN}=10 R_G=6Ω		8	20	nS
	t_r			12	30	
Turn-Off Time	$t_{d(off)}$			17	35	
	t_f			8	20	

TYPICAL CHARACTERISTICS

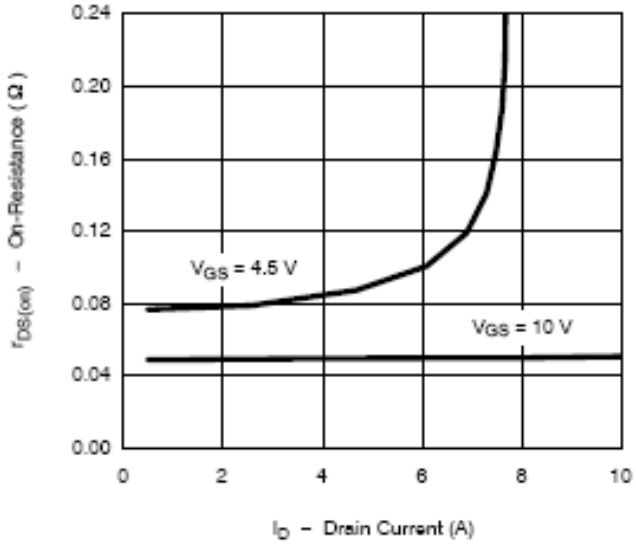
Output Characteristics



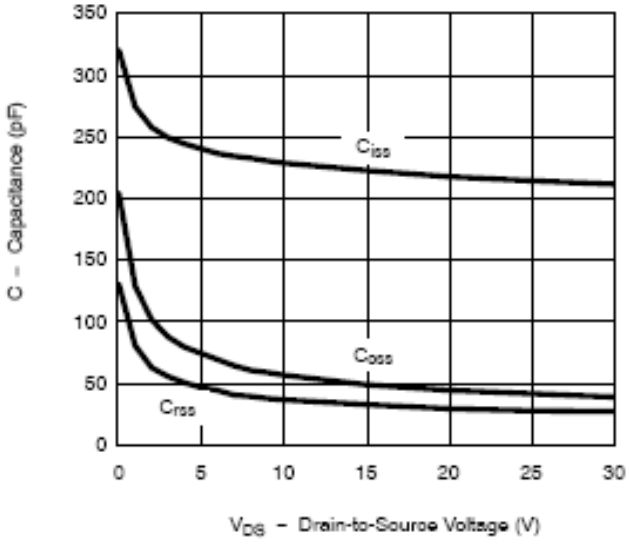
Transfer Characteristics



On-Resistance vs. Drain Current

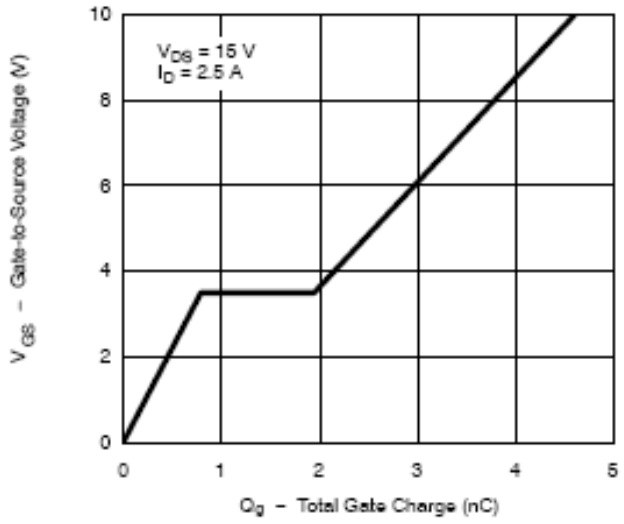


Capacitance

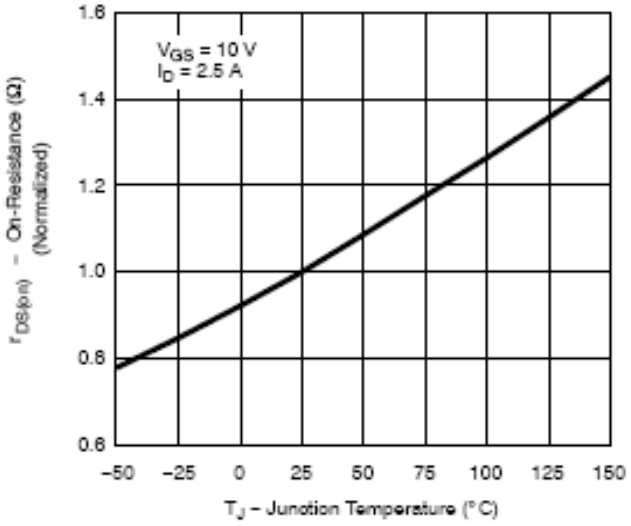


TYPICAL CHARACTERISTICS

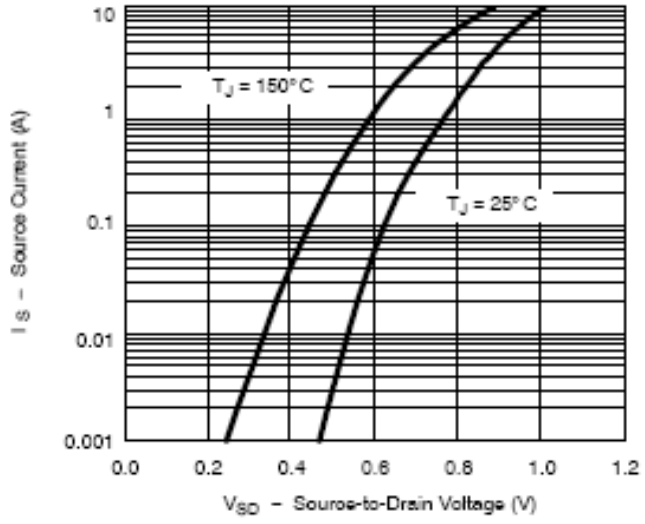
Gate Charge



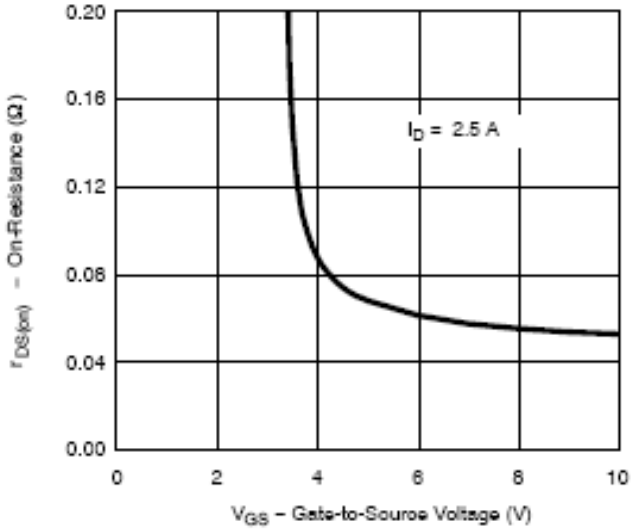
On-Resistance vs. Junction Temperature



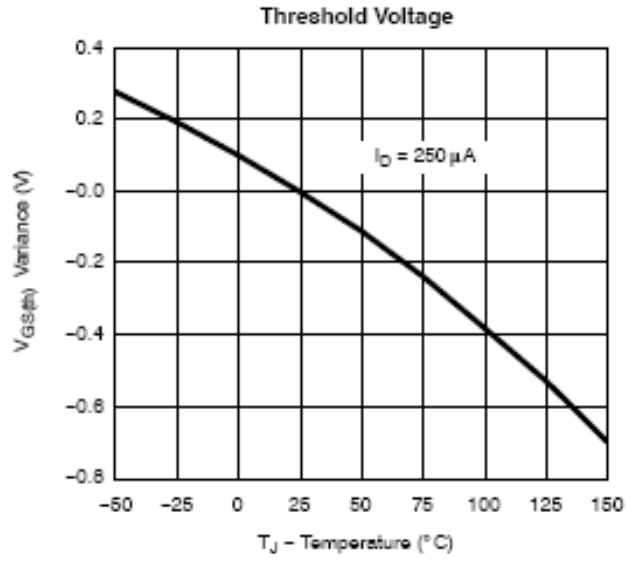
Source-Drain Diode Forward Voltage

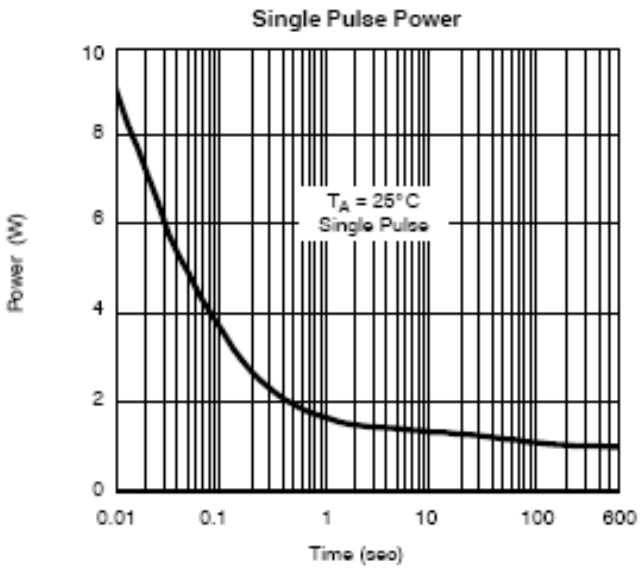


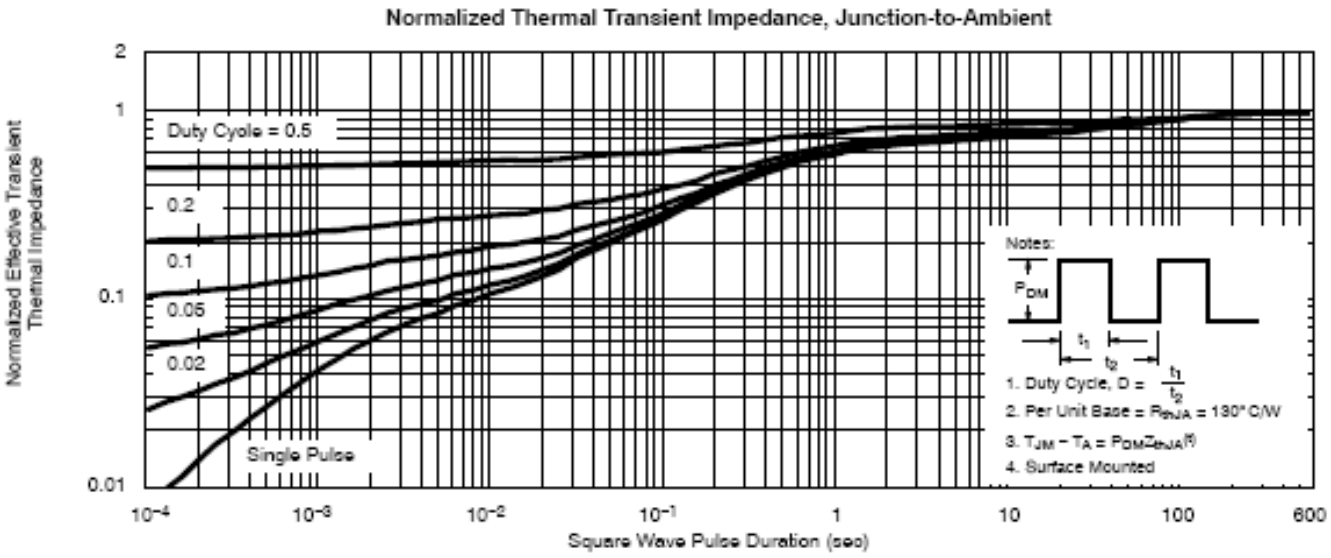
On-Resistance vs. Gate-to-Source Voltage



TYPICAL CHARACTERISTICS







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